Victor Mikheev

List of Publications by Year in descending order

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		1937685	2053705
16	29	4	5
papers	citations	h-index	g-index
16	16	16	7
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Concentration maxima of the mobility of 2D electrons scattered by correlated impurity ions in thin doped layers. Low Temperature Physics, 2019, 45, 123-127.	0.6	O
2	The effects of illumination on the mobility of 2D electrons during scattering by a correlated distribution of impurity ions. Low Temperature Physics, 2017, 43, 499-503.	0.6	0
3	Influence of the form of structure factor on the mobility of nondegenerate two-dimensional electrons. Physics of the Solid State, 2014, 56, 546-553.	0.6	О
4	Mobility of nondegenerate two-dimensional electrons in scattering by a correlated distribution of impurity ions. Physics of the Solid State, 2013, 55, 559-566.	0.6	2
5	Influence of correlations in a flat distribution of impurity ions on the mobility of two-dimensional electrons at low temperatures. Physics of the Solid State, 2012, 54, 1451-1458.	0.6	3
6	Mobility of 2D-electrons in scattering on a correlated distribution of impurity ions in doped thin layers. Physics of the Solid State, 2011, 53, 864-871.	0.6	4
7	Temperature features of electrical resistivity of two-dimensional electrons in scattering by a correlated distribution of impurity ions in doped thin layers. Physics of the Solid State, 2011, 53, 2210-2219.	0.6	3
8	Maximum of the mobility of two-dimensional electrons upon scattering by a correlated distribution of impurity ions. Physics of the Solid State, 2008, 50, 1957-1963.	0.6	5
9	Mobility of two-dimensional electrons upon scattering by a correlated distribution of impurity ions. Physics of the Solid State, 2007, 49, 1856-1866.	0.6	6
10	Simulation of Spatial Correlations of Impurity Ions in Solids Using Configurational Entropy and the Hard-Sphere Model. Physics of the Solid State, 2005, 47, 1091.	0.6	4
11	Giant low-temperature thermal resistance of ZnSeNi. Physics of the Solid State, 2003, 45, 236-239.	0.6	0
12	Mobility of electrons upon scattering by a multicomponent correlated system of impurity centers. Physics of the Solid State, 2001, 43, 430-438.	0.6	1
13	Temperature effect on spatial correlations of impurity ions in HgSe: Fe crystals. Physics of the Solid State, 2001, 43, 1860-1866.	0.6	0
14	Spatial correlation of impurity ions in solids. Physics of the Solid State, 1999, 41, 1830-1833.	0.6	0
15	Influence of donor-donor interaction on the metal-insulator transition in doped semiconductors. Physics of the Solid State, 1997, 39, 1774-1778.	0.6	1
16	Impurity Scattering in Weakly Compensated Gapless Semiconductors at Low Temperatures. Physica Status Solidi (B): Basic Research, 1989, 156, 577-582.	1.5	0